

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	I_D $T_A = 25^\circ C$
30V	760m Ω @ $V_{GS} = 4.5V$	0.65A
	930m Ω @ $V_{GS} = 2.5V$	0.58A
	1500m Ω @ $V_{GS} = 1.8V$	0.45A

Description

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Load switch
- Portable applications
- Power Management Functions

Features

- 0.4mm ultra low profile package for thin application
- 0.48mm² package footprint, 16 times smaller than SOT23
- Low $V_{GS(th)}$, can be driven directly from a battery
- Low $R_{DS(on)}$
- **ESD Protected**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

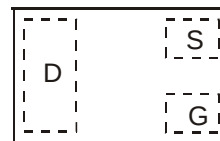
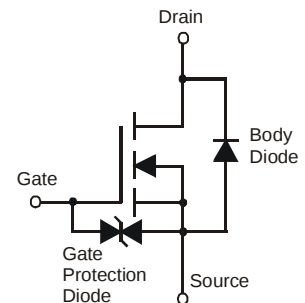
- Case: X2-DFN0806-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208 ^(e4)
- Weight: 0.00043 grams (approximate)



X2-DFN0806-3



Bottom View


 Top View
 Package Pin Configuration


Equivalent Circuit

Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DMN3900UFA-7B	NU	7	8	10,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information

DMN3900UFA-7B


 Top View
 Bar Denotes Gate
 and Source Side

NU = Product Type Marking Code

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±8	
Continuous Drain Current	V _{GS} = 4.5V	(Note 6)	I _D	0.65	A
		T _A = +70°C (Note 6)		0.52	
		(Note 5)	I _D	0.55	
Pulsed Drain Current		(Note 7)	I _{DM}	2.5	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 6)	P _D	490	mW
	(Note 5)		390	
Thermal Resistance, Junction to Ambient	(Note 6)	R _{θJA}	255	°C/W
	(Note 5)		327	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	-	-	1	μA	V _{DS} = 30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	3	μA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(th)}	0.45	-	0.95	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance (Note 8)	R _{DS(on)}	-	-	760	mΩ	V _{GS} = 4.5V, I _D = 200mA
				930		V _{GS} = 2.5V, I _D = 100mA
				1500		V _{GS} = 1.8V, I _D = 75mA
Forward Transfer Admittance	Y _{fs}	40	-	-	mS	V _{DS} = 3V, I _D = 10mA
Diode Forward Voltage (Note 8)	V _{SD}	-	0.7	1.2	V	V _{GS} = 0V, I _S = 300mA
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	-	42.2	-	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	-	4.5	-	pF	
Reverse Transfer Capacitance	C _{rss}	-	3.4	-	pF	
Gate Resistance	R _g	-	468	-	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _g	-	0.7	-	nC	V _{GS} = 4.5V, V _{DS} = 15V, I _D = 200mA
Gate-Source Charge	Q _{gs}	-	0.11	-	nC	
Gate-Drain Charge	Q _{gd}	-	0.15	-	nC	
Turn-On Delay Time	t _{D(on)}	-	10.5	-	ns	V _{DS} = 10V, I _D = 200mA, V _{GS} = 4.5V, R _G = 6Ω
Turn-On Rise Time	t _r	-	7.8	-	ns	
Turn-Off Delay Time	t _{D(off)}	-	80.6	-	ns	
Turn-Off Fall Time	t _f	-	23.4	-	ns	

- Notes:
- For a device surface mounted on a minimum recommended pad layout of an FR4 PCB, in still air conditions; the device is measured when operating in steady-state condition.
 - Same as note 4, except the device measured at t ≤ 10 sec.
 - Same as note 4, except the device is pulsed at duty cycle of 1% for a pulse width of 10μs.
 - Measured under pulsed conditions to minimize self-heating effect. Pulse width ≤ 300μs; duty cycle ≤ 2%.
 - For design aid only, not subject to production testing.

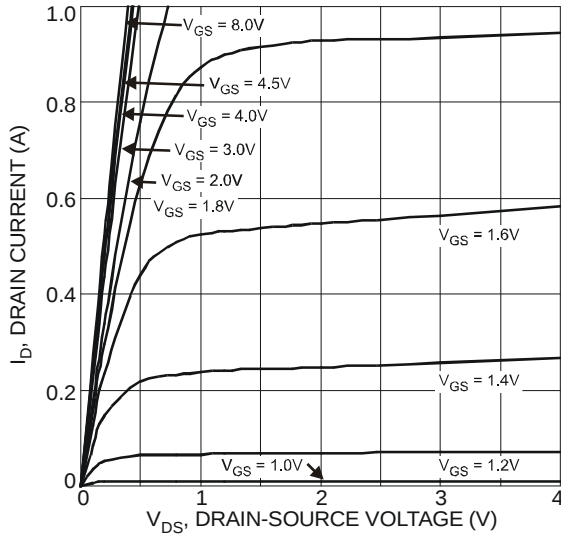


Fig. 1 Typical Output Characteristic

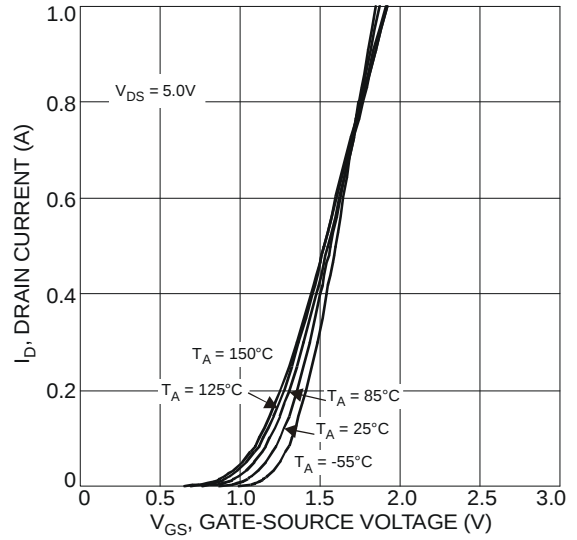


Fig. 2 Typical Transfer Characteristics

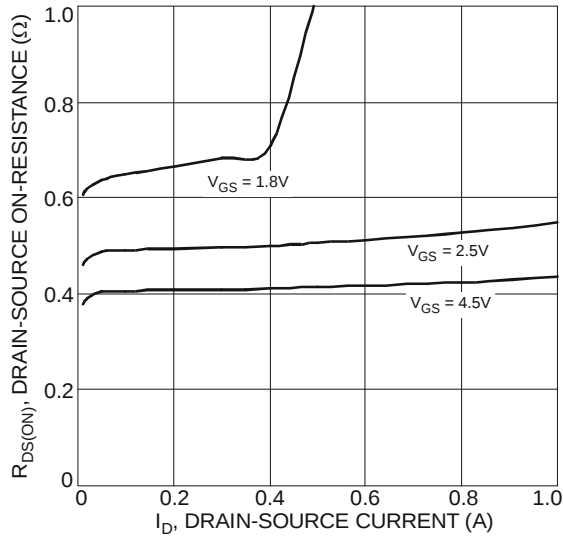


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

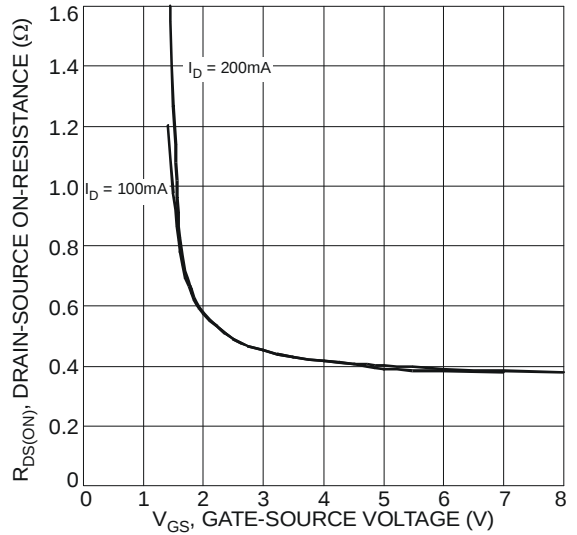


Fig. 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

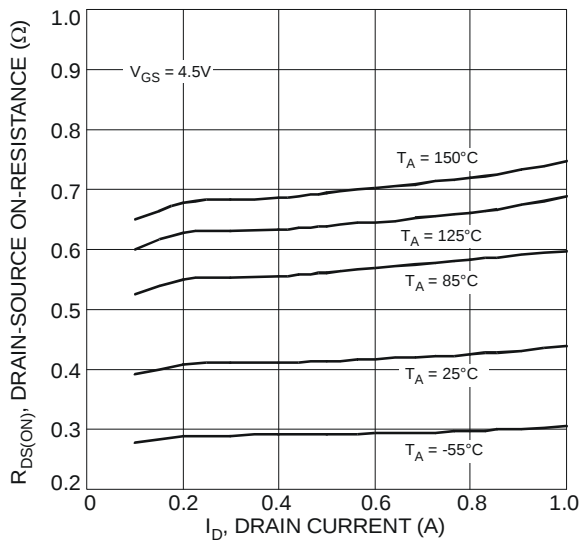


Fig. 5 Typical On-Resistance vs. Drain Current and Temperature

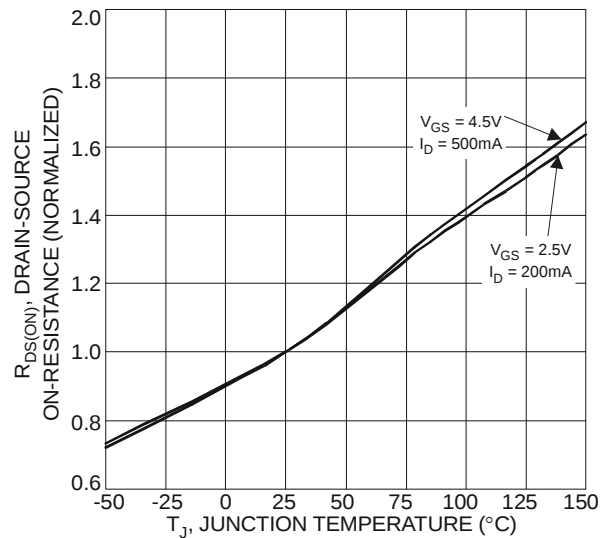


Fig. 6 On-Resistance Variation with Temperature

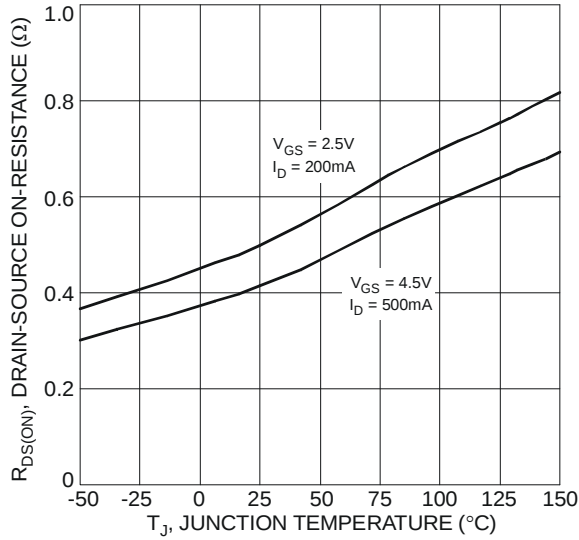


Fig. 7 On-Resistance Variation with Temperature

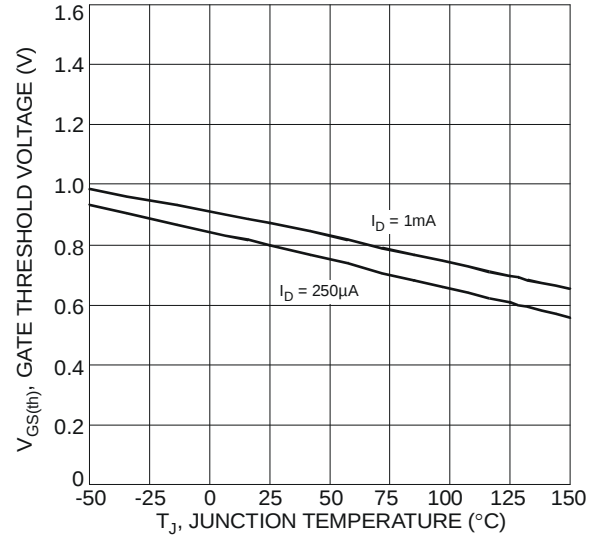


Fig. 8 Gate Threshold Variation vs. Ambient Temperature

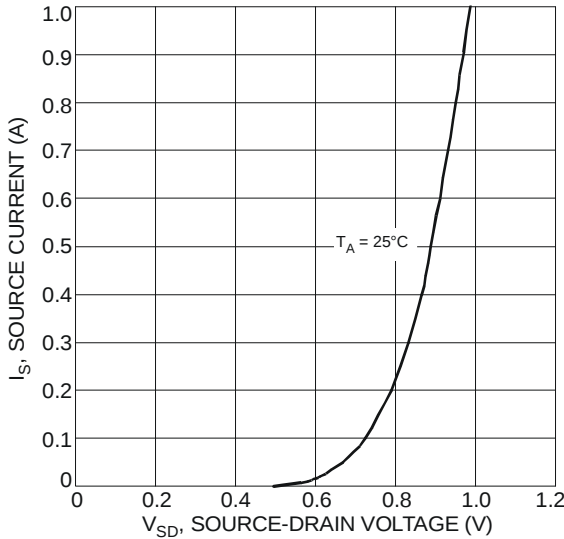


Fig. 9 Diode Forward Voltage vs. Current

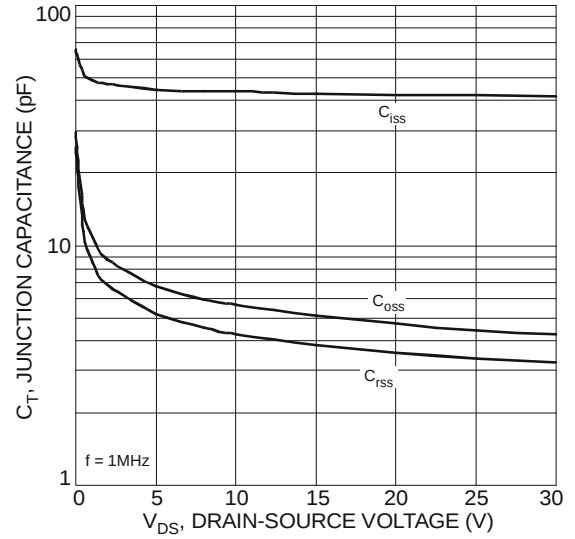


Fig. 10 Typical Junction Capacitance

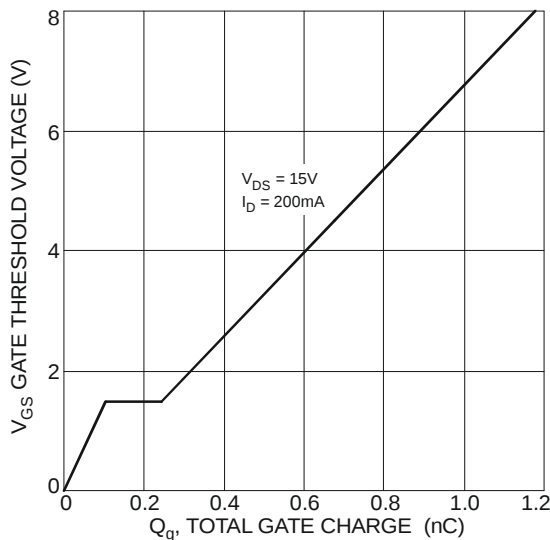


Fig. 11 Gate Charge

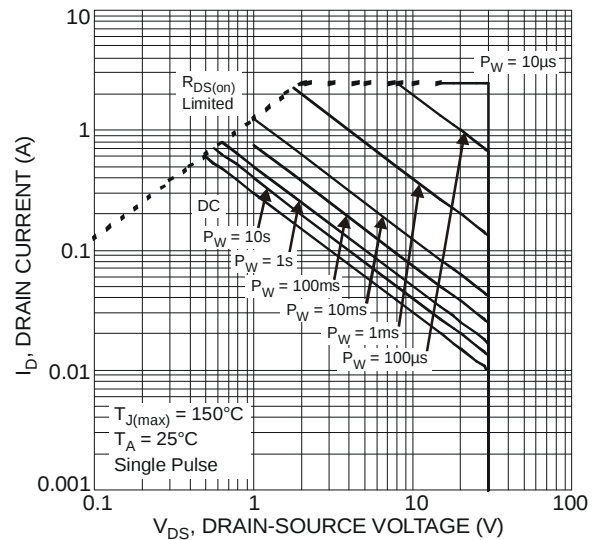
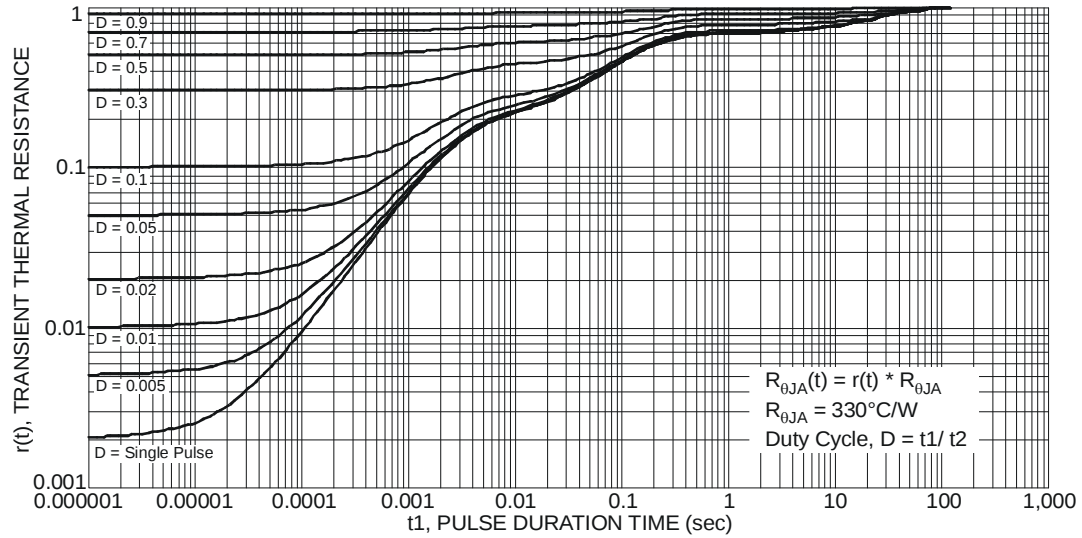
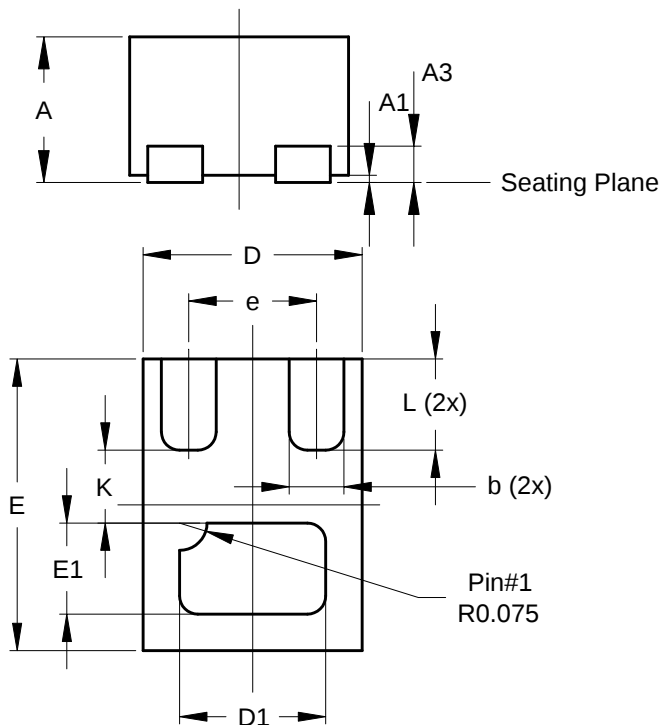


Fig. 12 SOA, Safe Operation Area



Package Outline Dimensions

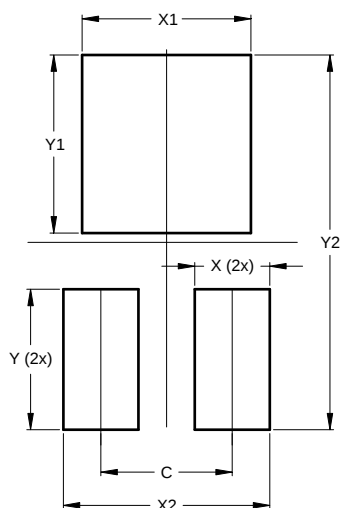
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



X2-DFN0806-3			
Dim	Min	Max	Typ
A	0.375	0.40	0.39
A1	0	0.05	0.02
A3	-	-	0.10
b	0.10	0.20	0.15
D	0.55	0.65	0.60
D1	0.35	0.45	0.40
E	0.75	0.85	0.80
E1	0.20	0.30	0.25
e	-	-	0.35
K	-	-	0.20
L	0.20	0.30	0.25
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	0.350
X	0.200
X1	0.450
X2	0.550
Y	0.375
Y1	0.475
Y2	1.000

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